STARPOWER

SEMICONDUCTOR **IGBT**

GD50PIT120C6S

Molding Type Module

1200V/50A PIM in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

- Low $V_{CE(sat)}$ trench IGBT technology
- 10μs short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175℃
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

IGBT-inverter T_C=25℃ unless otherwise noted

Maximum Rated Values

Symbol	Description	GD50PIT120C6S	Units
V_{CES}	Collector-Emitter Voltage @ T_j=25℃	1200	V
V_{GES}	Gate-Emitter Voltage @ T_j=25℃	±30	V
I_C	Collector Current @ T_C=25℃ @ T_C=100℃	90 50	A
I_{CM}	Pulsed Collector Current t_p=1ms	100	A
P_{tot}	Total Power Dissipation @ T_j=175℃	340	W

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	T_j=25℃	1200			V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25℃			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25℃			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=2.4mA,V_{CE}=V_{GE}, T_j=25℃	5.0	6.1	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=50A,V_{GE}=15V, T_j=25℃		1.90	2.35	V
		I_C=50A,V_{GE}=15V, T_j=125℃		2.30		
		I_C=50A,V_{GE}=15V, T_j=150℃		2.40		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=50A, R_G=18Ω,V_{GE}=±15V, T_j=25℃		534		ns
t_r	Rise Time			147		ns
$t_{d(off)}$	Turn-Off Delay Time			393		ns
t_f	Fall Time			181		ns
E_{on}	Turn-On Switching Loss			10.6		mJ
E_{off}	Turn-Off Switching Loss			2.67		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=50A, R_G=18Ω,V_{GE}=±15V, T_j=125℃		546		ns
t_r	Rise Time			162		ns
$t_{d(off)}$	Turn-Off Delay Time			412		ns
t_f	Fall Time			306		ns
E_{on}	Turn-On Switching Loss			12.1		mJ
E_{off}	Turn-Off Switching Loss			3.81		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=50A, R_G=18Ω,V_{GE}=±15V, T_j=150℃		554		ns
t_r	Rise Time			168		ns
$t_{d(off)}$	Turn-Off Delay Time			453		ns
t_f	Fall Time			329		ns
E_{on}	Turn-On Switching Loss			14.9		mJ
E_{off}	Turn-Off Switching Loss			4.26		mJ
C_{ies}	Input Capacitance	V_{CE}=30V,f=1Mhz, V_{GE}=0V		6.24		nF
C_{oes}	Output Capacitance			0.23		nF
C_{res}	Reverse Transfer Capacitance			0.15		nF
Q_G	Gate Charge	V_{CC}=600V,I_C=50A, V_{GE}=15V		290		nC
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=125℃,V_{CC}=900V, V_{CEM}≤1200V		500		A

Diode-inverter T_C=25℃ unless otherwise noted

Maximum Rated Values

Symbol	Description	GD50PIT120C6S	Units
V_{RRM}	Repetitive Peak Reverse Voltage @ T_j=25℃	1200	V
I_F	DC Forward Current	50	A
I_{FRM}	Repetitive Peak Forward Current t_p=1ms	100	A

Characteristics Values

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=50A,V_{GE}=0V	T_j=25℃		1.80	2.20	V
			T_j=125℃		1.85		
			T_j=150℃		1.90		
Q_r	Recovered Charge	I_F=50A, V_R=600V, R_G=18Ω, V_{GE}=-15V	T_j=25℃		3.0		μC
			T_j=125℃		6.6		
			T_j=150℃		10.8		
I_{RM}	Peak Reverse Recovery Current		T_j=25℃		19		A
			T_j=125℃		27		
			T_j=150℃		30		
E_{rec}	Reverse Recovery Energy		T_j=25℃		0.94		mJ
			T_j=125℃		2.18		
			T_j=150℃		4.12		

Diode-rectifier T_C=25℃ unless otherwise noted

Maximum Rated Values

Symbol	Description	GD50PIT120C6S	Units
V_{RRM}	Repetitive Peak Reverse Voltage @ T_j=25℃	1600	V
$I_{F(AV)}$	Average On-state Current @ T_C=100℃	59	A
I_{RMSM}	Maximum RMS Current At Rectifier Output @ T_C=80℃	85	A
I_{FSM}	Surge Forward Current V_R=0V,t_p=10ms,T_j=45℃	850	A
I^2t	I^2t-value,V_R=0V,t_p=10ms,T_j=45℃	3610	A^2s

Characteristics Values

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=50A	T_j=150℃		1.10		V
I_R	Reverse Current	T_j=150℃,V_R=1600V				1.5	mA

IGBT-brake-chopper T_C=25℃ unless otherwise noted

Maximum Rated Values

Symbol	Description	GD50PIT120C6S	Units
V_{CES}	Collector-Emitter Voltage @ T_j=25℃	1200	V
V_{GES}	Gate-Emitter Voltage @ T_j=25℃	±30	V
I_C	Collector Current @ T_C=25℃ @ T_C=100℃	50 25	A
I_{CM}	Pulsed Collector Current t_p=1ms	50	A
P_{tot}	Total Power Dissipation @ T_j=175℃	231	W

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	T_j=25℃	1200			V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25℃			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25℃			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=1.2mA,V_{CE}=V_{GE}, T_j=25℃	5.0	6.3	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=25A,V_{GE}=15V, T_j=25℃		1.90	2.35	V
		I_C=25A,V_{GE}=15V, T_j=125℃		2.30		
		I_C=25A,V_{GE}=15V, T_j=150℃		2.40		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=25A, R_G=33Ω,V_{GE}=±15V, T_j=25℃		233		ns
t_r	Rise Time			66		ns
$t_{d(off)}$	Turn-Off Delay Time			184		ns
t_f	Fall Time			208		ns
E_{on}	Turn-On Switching Loss			3.06		mJ
E_{off}	Turn-Off Switching Loss			1.16		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=25A, R_G=33Ω,V_{GE}=±15V, T_j=125℃		310		ns
t_r	Rise Time			86		ns
$t_{d(off)}$	Turn-Off Delay Time			217		ns
t_f	Fall Time			324		ns
E_{on}	Turn-On Switching Loss			3.50		mJ
E_{off}	Turn-Off Switching Loss			1.78		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=25A, R_G=33Ω,V_{GE}=±15V, T_j=150℃		221		ns
t_r	Rise Time			68		ns
$t_{d(off)}$	Turn-Off Delay Time			225		ns
t_f	Fall Time			347		ns
E_{on}	Turn-On Switching Loss			4.45		mJ
E_{off}	Turn-Off Switching Loss			2.02		mJ
C_{ies}	Input Capacitance	V_{CE}=30V,f=1Mhz, V_{GE}=0V		3.43		nF
C_{oes}	Output Capacitance			0.13		nF
C_{res}	Reverse Transfer Capacitance			0.08		nF
Q_G	Gate Charge	V_{CC}=600V,I_C=25A, V_{GE}=15V		160		nC
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=125℃,V_{CC}=900V, V_{CEM}≤1200V		225		A

Diode-brake-chopper T_C=25℃ unless otherwise noted

Maximum Rated Values

Symbol	Description	GD50PIT120C6S	Units
V_{RRM}	Repetitive Peak Reverse Voltage @ T_j=25℃	1200	V
I_F	DC Forward Current	25	A
I_{FRM}	Repetitive Peak Forward Current t_p=1ms	50	A

Characteristics Values

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=25A,V_{GE}=0V	T_j=25℃		1.78	2.18	V
			T_j=125℃		1.88		
			T_j=150℃		1.91		
Q_r	Recovered Charge	I_F=25A, V_R=600V, R_G=33Ω, V_{GE}=-15V	T_j=25℃		1.1		μC
			T_j=125℃		3.2		
			T_j=150℃		4.5		
I_{RM}	Peak Reverse Recovery Current		T_j=25℃		17		A
			T_j=125℃		21		
			T_j=150℃		28		
E_{rec}	Reverse Recovery Energy		T_j=25℃		0.80		mJ
			T_j=125℃		1.38		
			T_j=150℃		1.96		

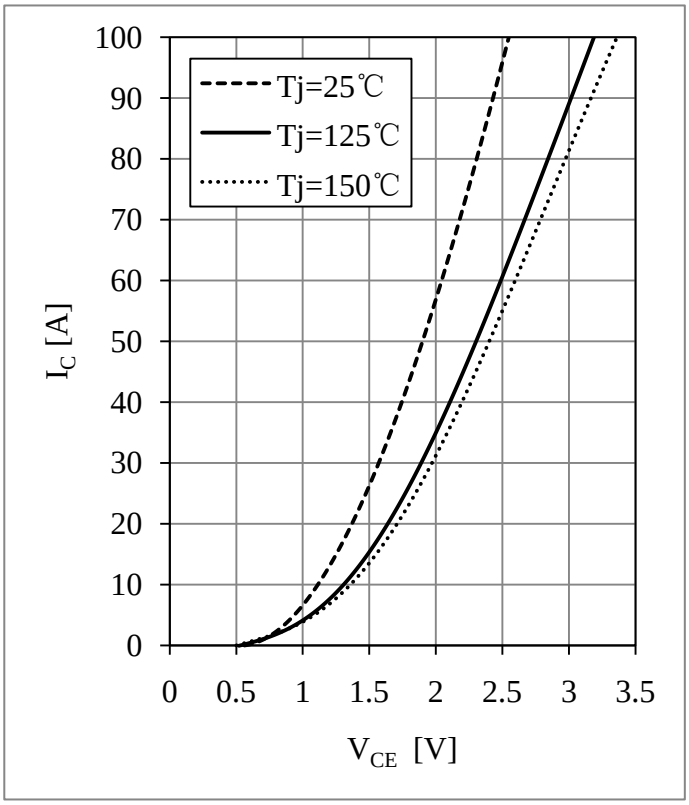
Electrical Characteristics of NTC T_C=25℃ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R_{25}	Rated Resistance			5.0		kΩ
ΔR/R	Deviation of R_{100}	T_C=100℃,R_{100}=493.3Ω	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

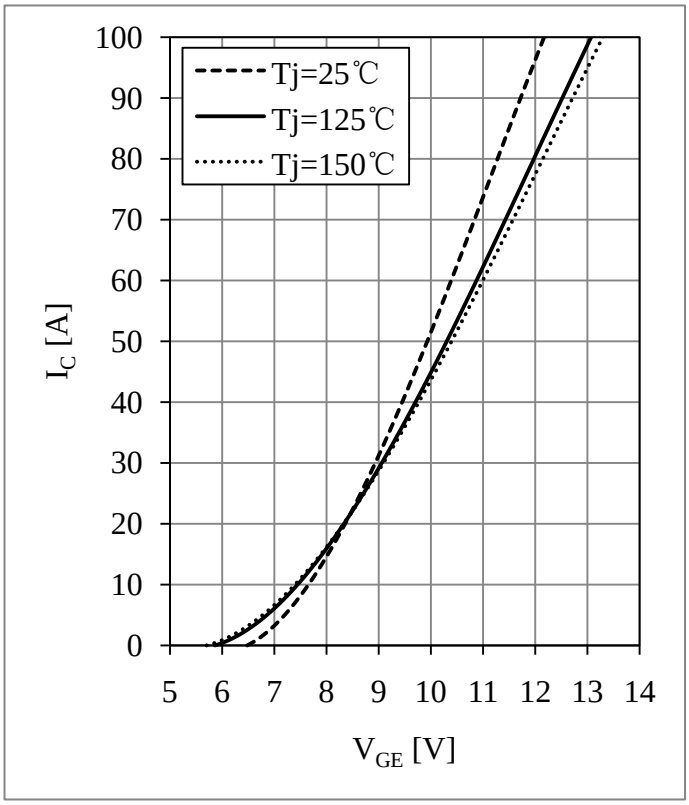
IGBT Module

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	2500			V
L_{CE}	Stray Inductance		60		nH
$R_{CC'+EE'}$ $R_{AA'+CC'}$	Module Lead Resistance,Terminal to Chip @ T_C=25℃		4.00 2.00		mΩ
$R_{\theta JC}$	Junction-to-Case (per IGBT-inverter) Junction-to-Case (per Diode-inverter) Junction-to-Case (per Diode-rectifier) Junction-to-Case (per IGBT-brake-chopper) Junction-to-Case (per Diode-brake-chopper)			0.441 0.614 0.636 0.649 0.949	K/W
$R_{\theta CS}$	Case-to-Sink (per IGBT-inverter) Case-to-Sink (per Diode-inverter) Case-to-Sink (per Diode-rectifier) Case-to-Sink (per IGBT-brake-chopper) Case-to-Sink (per Diode-brake-chopper)		0.312 0.435 0.450 0.460 0.672		
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)		0.009		K/W
T_{jmax}	Maximum Junction Temperature (inverter, brake) Maximum Junction Temperature(rectifier)			175 150	℃
T_{jop}	Operating Junction Temperature (inverter, brake) Operating Junction Temperature(rectifier)	-40 -40		150 125	℃
T_{STG}	Storage Temperature Range	-40		125	℃
Mounting Torque	Mounting Screw:M5	3.0		6.0	N.m
G	Weight of Module		300		g

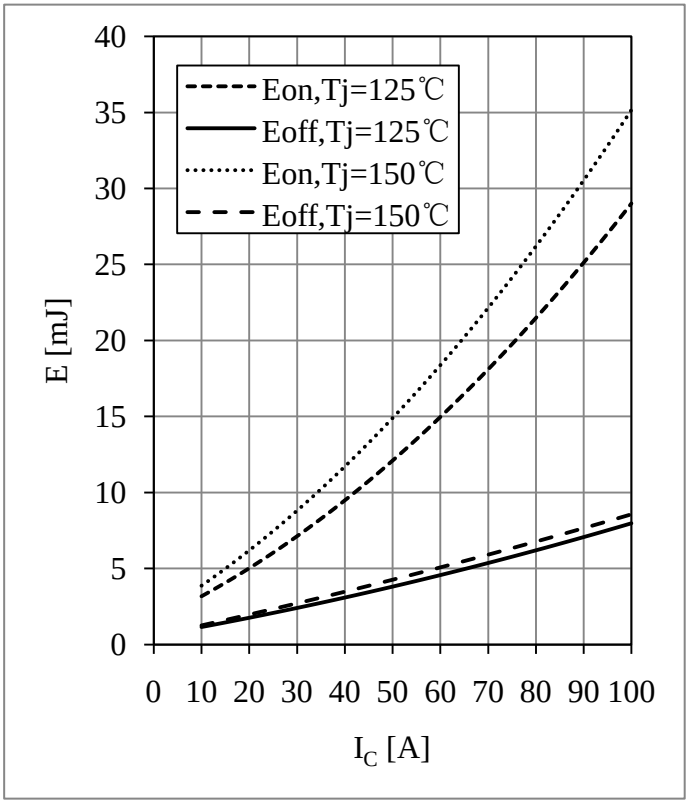
IGBT-inverter Output Characteristics
V_{GE}=15V



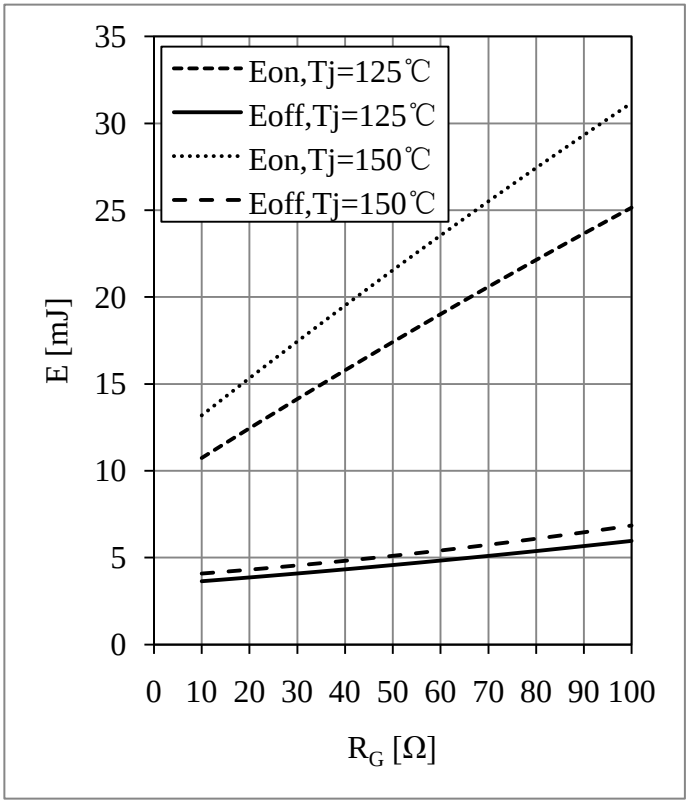
IGBT-inverter Transfer Characteristics
V_{CE}=20V



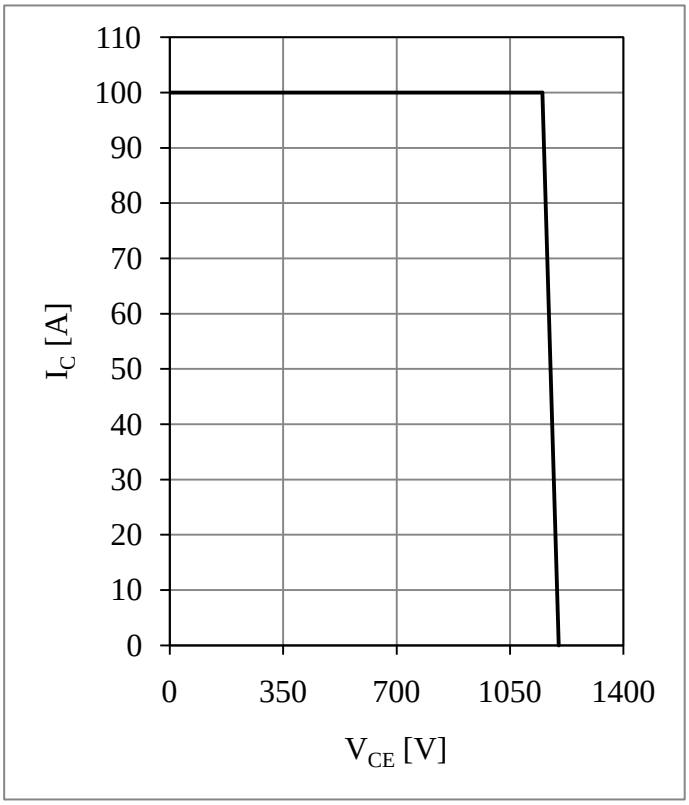
IGBT-inverter Switching Loss vs. I_C
V_{CC}=600V,R_G=18Ω,V_{GE}=±15V



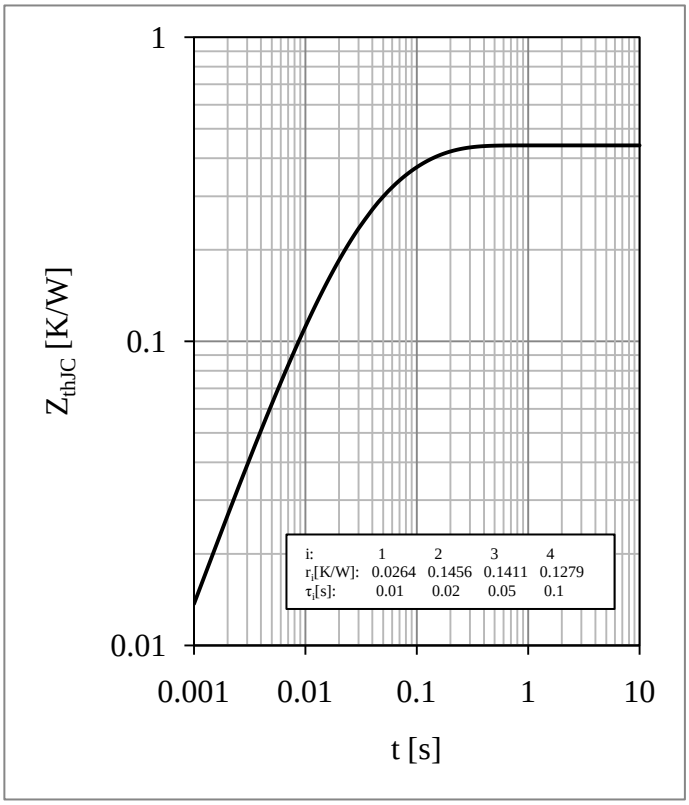
IGBT-inverter Switching Loss vs. R_G
V_{CC}=600V,I_C=50A,V_{GE}=±15V



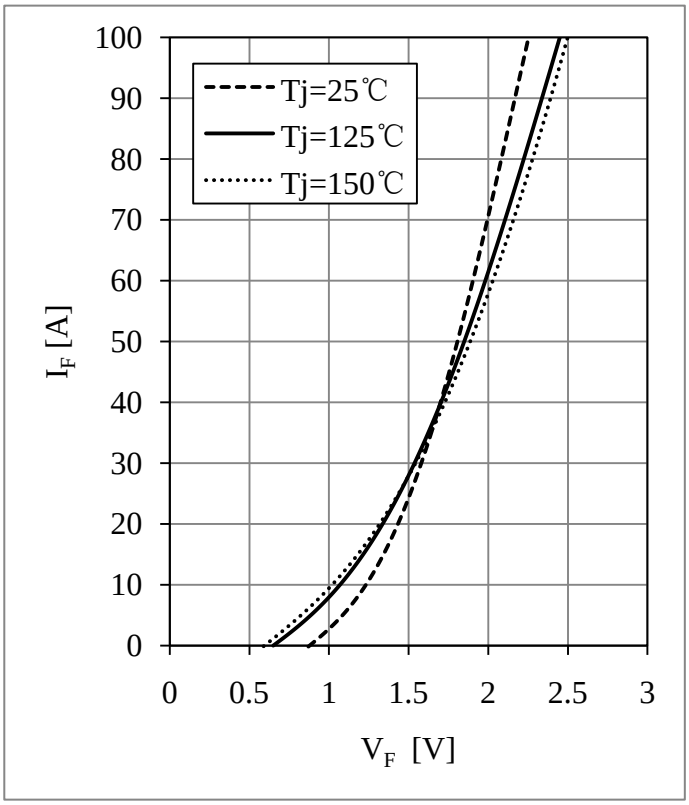
IGBT-inverter RBSOA
Module, R_G=18Ω,V_{GE}=±15V,T_j=150℃



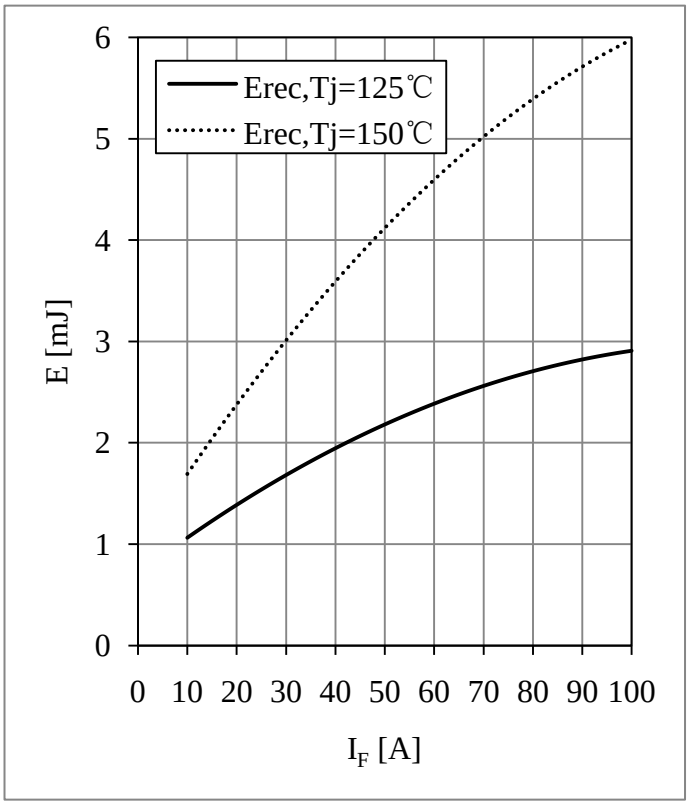
IGBT-inverter Transient Thermal Impedance



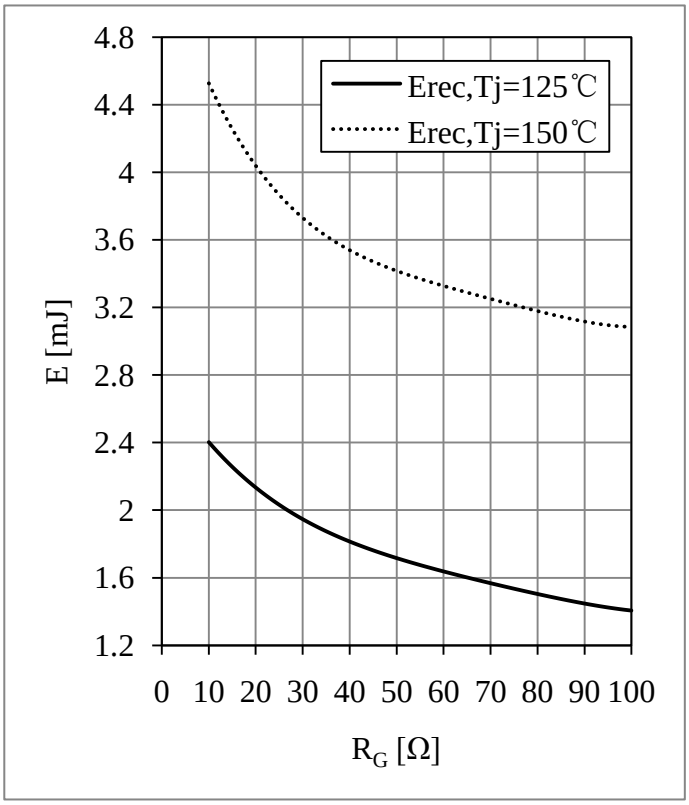
Diode-inverter Forward Characteristics



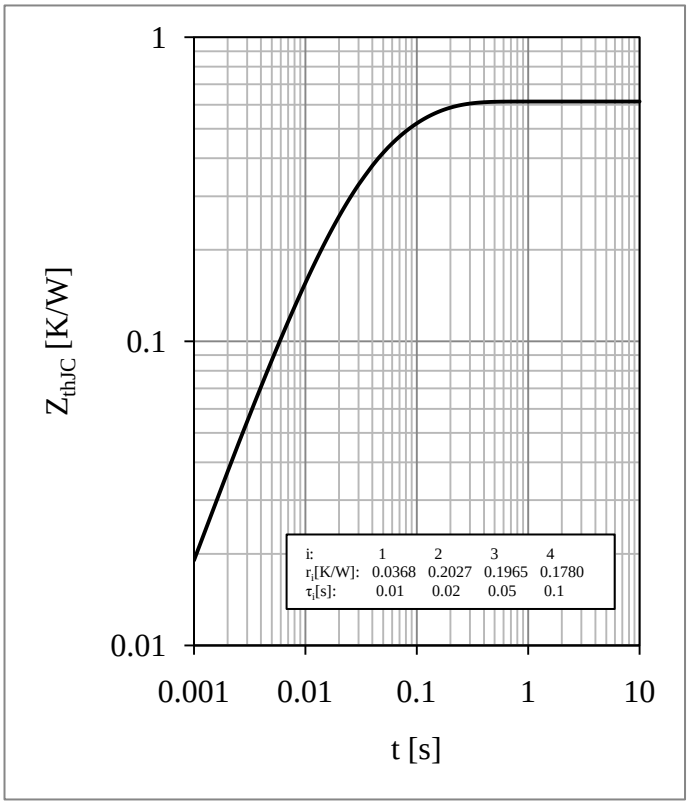
Diode-inverter Switching Loss vs. I_F
V_{CC}=600V,R_G=18Ω



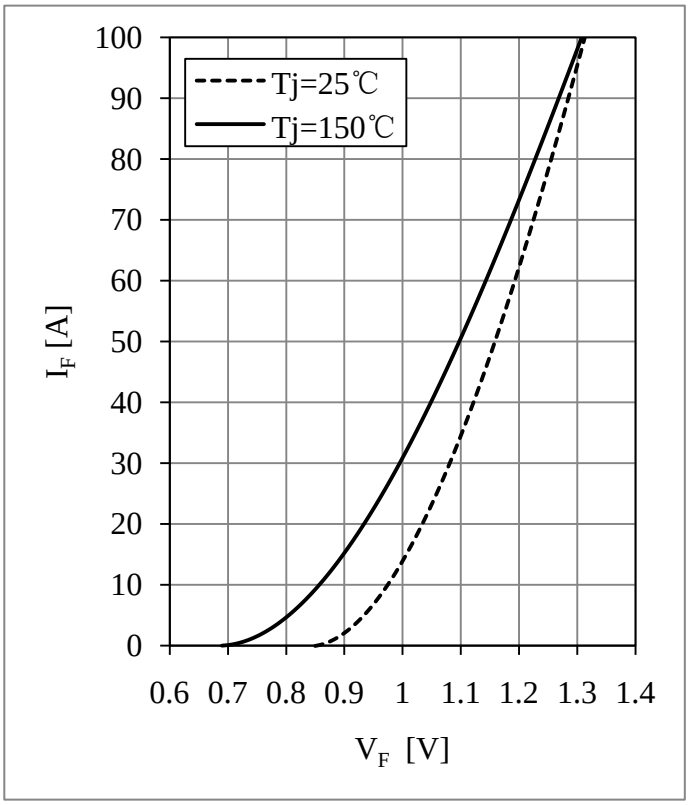
Diode-inverter Switching Loss vs. R_G
V_{CC}=600V,I_F=50A



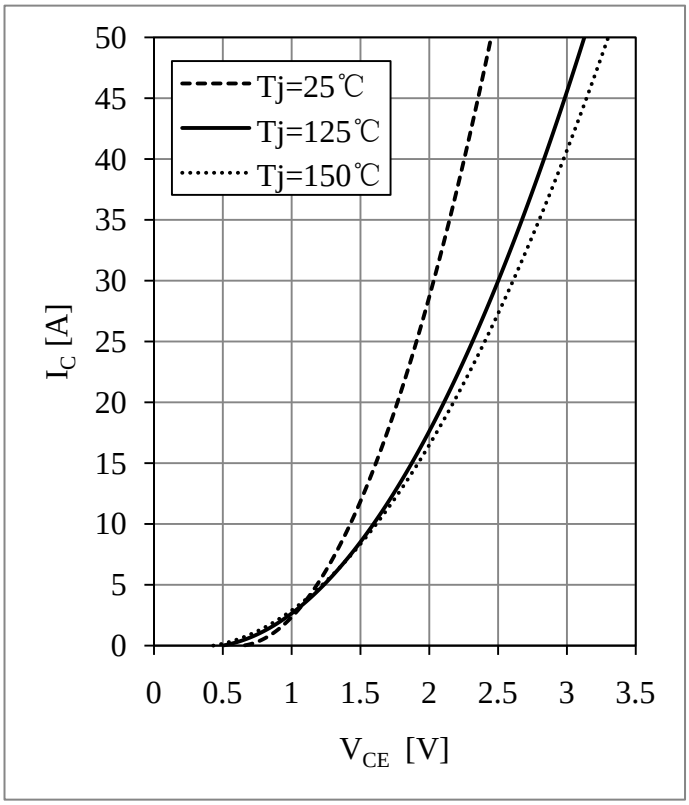
Diode-inverter Transient Thermal Impedance



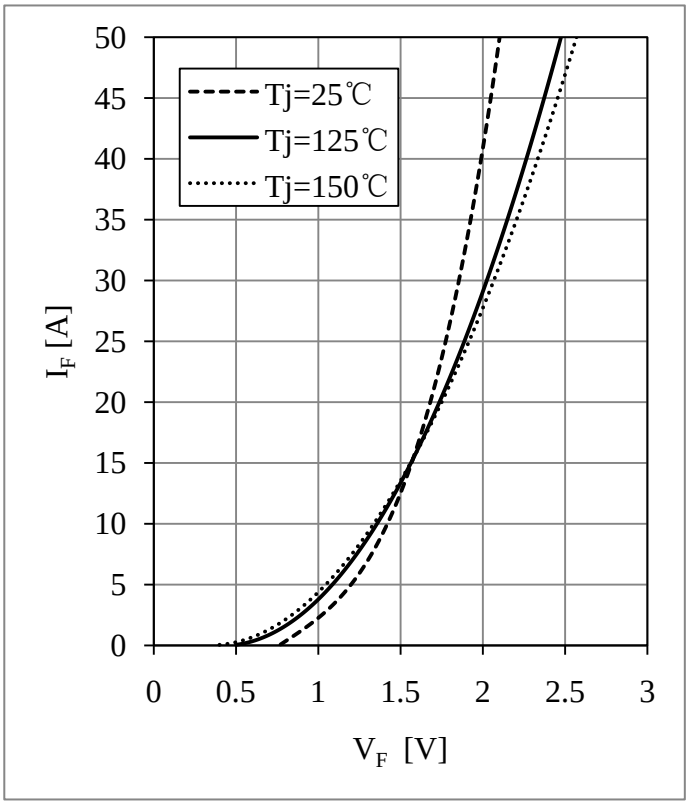
Diode-rectifier Forward Characteristics



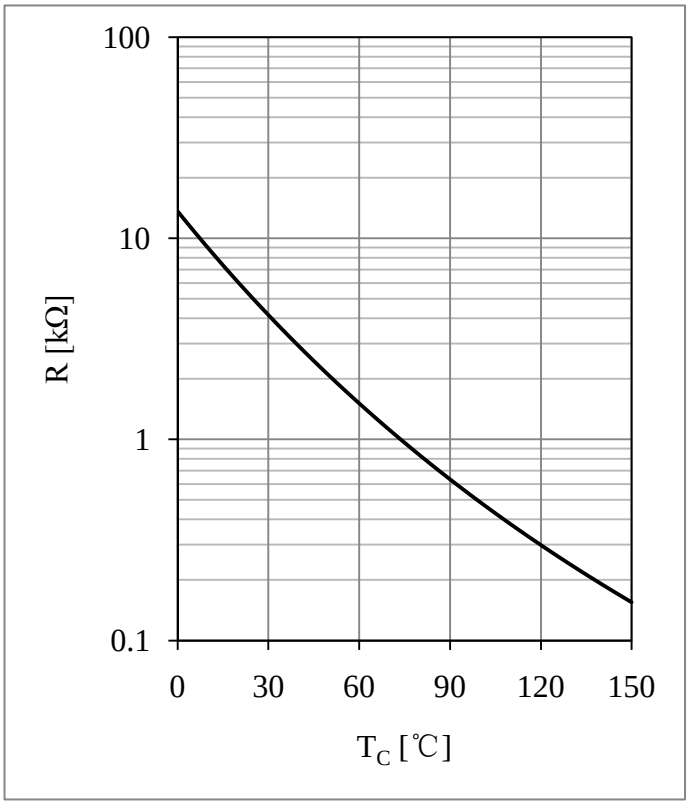
IGBT-brake-chopper Output Characteristics
V_{GE}=15V



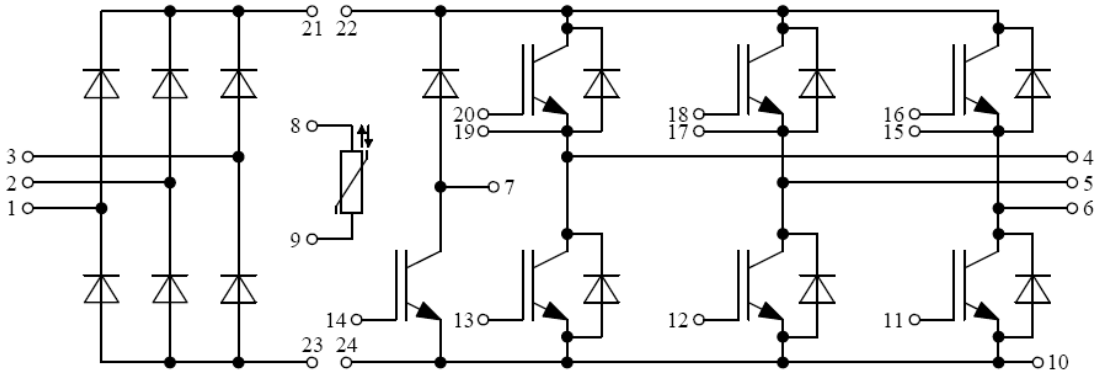
Diode-brake-chopper Forward Characteristics



NTC Temperature Characteristic

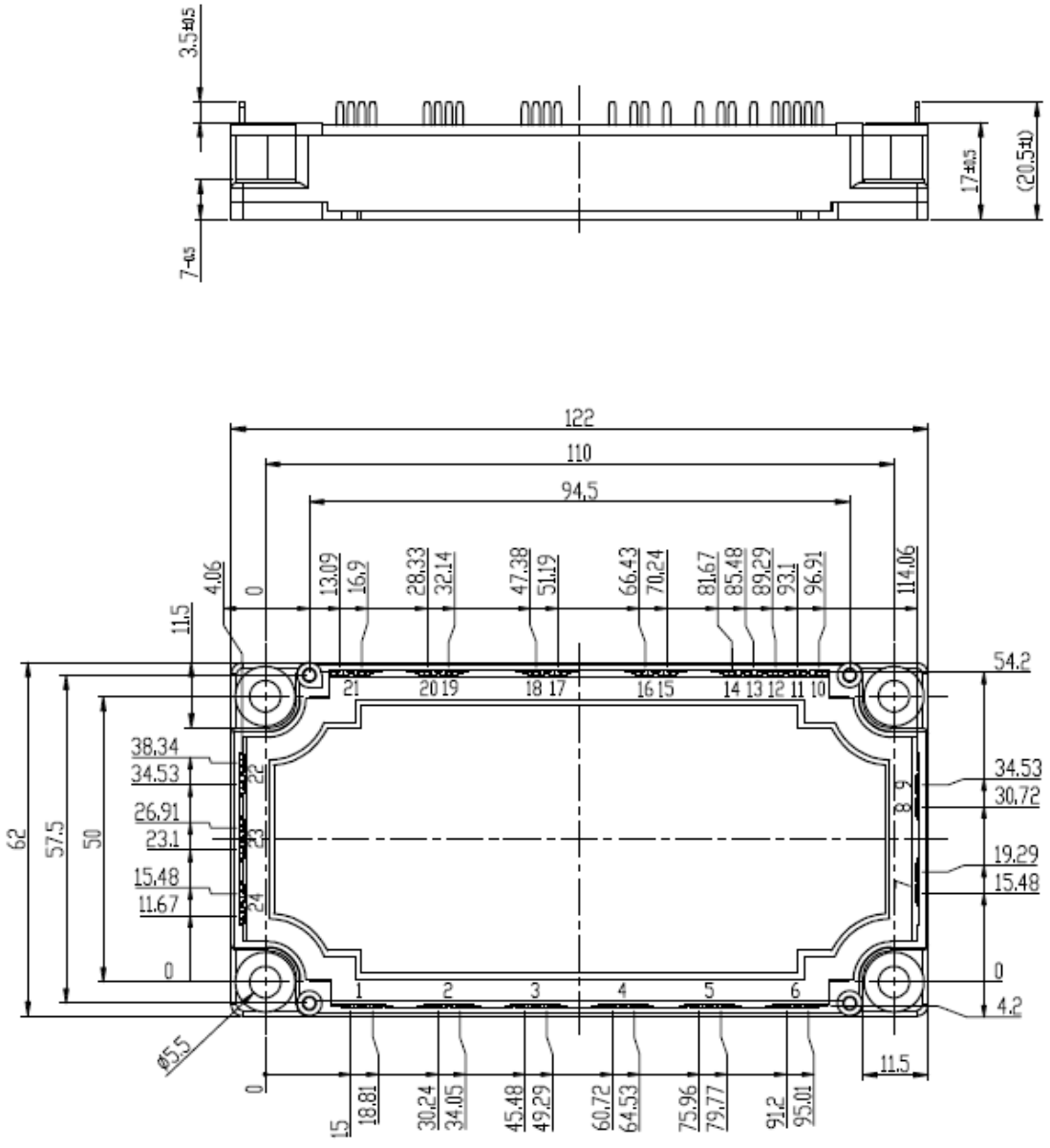


Equivalent Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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